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December 2013

# **FDP5800**

# N-Channel Logic Level PowerTrench $^{(\!R\!)}$ MOSFET 60 V, 80 A, 6 m $\Omega$

#### **Features**

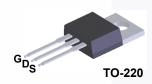
- $R_{DS(on)}$  = 4.6 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_{D}$  = 80 A
- High Performance Trench Technology for Extermly Low  $R_{\text{DS(on)}}$
- · Low Gate Charge
- · High Power and Current Handing Capability
- · RoHS Compliant

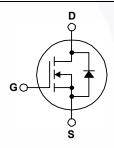
### **Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

### **Applications**

- · Power Tools
- · Motor Drives and Uninterruptible Power Supplies
- · Synchronous Rectification
- · Battery Protection Circuit





### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter			Unit
$V_{DSS}$	Drain-Source Voltage			60	V
V <sub>GSS</sub>	Gate-Source Voltage			±20	V
		- Continuous (T <sub>C</sub> = 25°C)		80	Α
$I_D$	Drain Current	- Continuous (T <sub>C</sub> = 100°C)		80*	A
		- Continuous (T <sub>A</sub> = 25°C)		14	Α
I <sub>DM</sub>	Drain Current	Drain Current - Pulsed			А
E <sub>AS</sub>	Single Pulsed Avalanch	ne Energy	(Note 1)	652	mJ
D	Power Dissipation	(T <sub>C</sub> = 25°C)		242	W
$P_{D}$		- Derate Above 25°C		1.61	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage	Temperature Range		-55 to +175	°C

<sup>\*</sup>Drain current limited by package.

#### **Thermal Characteristics**

Symbol	Parameter FDP5800			
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max.	0.62	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5			

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP5800	FDP5800	TO-220	Tube	N/A	N/A	50 units

## **Electrical Characteristics** $T_C$ = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
B <sub>VDSS</sub>	Drain-Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ}$	60			V
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 48 V			1	μΑ
IDSS	Zero Gate Voltage Drain Current	$V_{GS} = 0 \text{ V}$ $T_{J} = 150^{\circ}\text{C}$			500	μΑ
$I_{GSS}$	Gate-Body Leakage Current, Forward	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

#### On Characteristics

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	1.0		2.5	V
		V <sub>GS</sub> = 10 V , I <sub>D</sub> = 80 A		4.6	6.0	mΩ
		V <sub>GS</sub> =4.5 V , I <sub>D</sub> = 80 A		5.9	7.2	mΩ
R <sub>DS(on)</sub>	R <sub>DS(on)</sub> Static Drain-Source On Resistance	$V_{GS} = 5 \text{ V}$ , $I_{D} = 80 \text{ A}$		5.6	7.0	mΩ
		$V_{GS} = 10 \text{ V, } I_D = 80 \text{ A,}$ $T_J = 175^{\circ}\text{C}$		10.4	12.6	mΩ

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	\/ - 45 \/ \/ - 0 \	,	 6890	9160	pF
Coss	Output Capacitance	V <sub>DS</sub> = 15 V,V <sub>GS</sub> = 0 \ f = 1 MHz	٧,	 750	1000	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 – 1 1011 12		 295	445	pF
$R_G$	Gate Resistance	$V_{GS} = 0.5 \text{ V, f} = 1 \text{ MH}$	łz	 1.2		Ω
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS}$ = 0 V to 10 V		 112	145	nC
$Q_{g(TH)}$	Total Gate Charge at 5V	$V_{GS} = 0 V \text{ to } 5 V$	, ,,,,	 58		nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0 V \text{ to } 1 V$	/ <sub>DS</sub> = 30 V, I <sub>D</sub> = 80 A,	 7.0		nC
Q <sub>gs</sub>	Gate to Source Gate Charge		$I_D = 60 \text{ A},$ $I_D = 1 \text{ mA}$	 23		nC
Q <sub>gs2</sub>	Gate Charge Threshold to Plateau		·y · · · · ·	 13		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			 18		nC

## **Switching Characteristics** (V<sub>GS</sub> = 10V)

$t_{ON}$	Turn-On Time		/	37	85	ns
t <sub>d(on)</sub>	Turn-On Delay Time	.,		18	46	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD}$ = 30 V, $I_{D}$ = 80 A, $V_{GS}$ = 10 V, $R_{G}$ = 1.5 $\Omega$		19	47	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = 10 V, N <sub>G</sub> = 1.3 \(\frac{1}{2}\)		55	120	ns
t <sub>f</sub>	Turn-Off Fall Time			9	28	ns
t <sub>OFF</sub>	Turn-Off Time			64	138	ns

### **Drain-Source Diode Characteristics**

V Drai	V <sub>SD</sub> Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 80 \text{ A}$	-		1.25	V
V SD		$V_{GS} = 0 \text{ V}, I_{SD} = 40 \text{ A}$	-		1.0	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 60 A,		58		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	106		nC

Notes: 1: L = 1 mH, I $_{AS}$  = 36 A, V $_{DD}$  = 54 V, V $_{GS}$  = 10 V, R $_{G}$  = 25  $\Omega$ , Starting T $_{J}$  = 25 $^{o}$ C

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

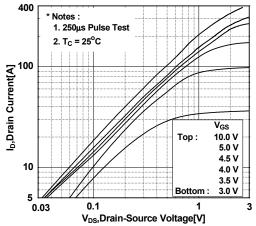


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

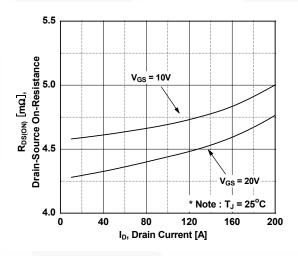


Figure 5. Capacitance Characteristics

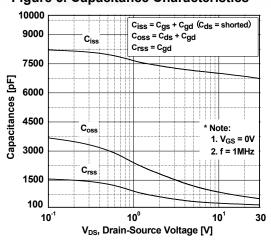


Figure 2. Transfer Characteristics

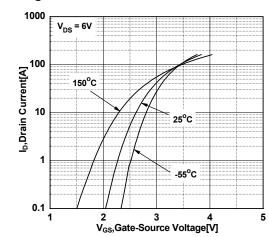


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

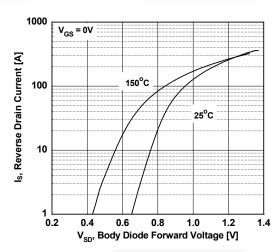
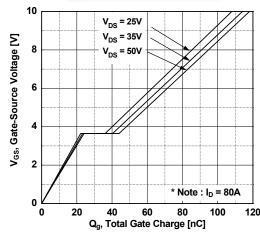


Figure 6. Gate Charge Characteristics



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

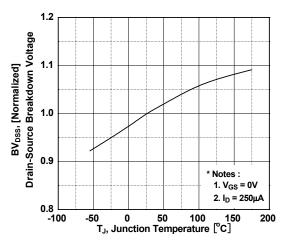


Figure 9. Maximum Safe Operating Area

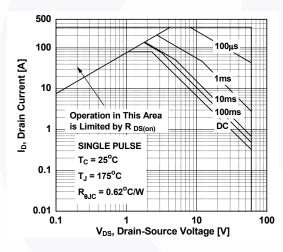


Figure 8. On-Resistance Variation vs. Temperature

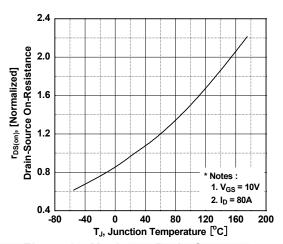


Figure 10. Maximum Drain Current vs. Case Temperature

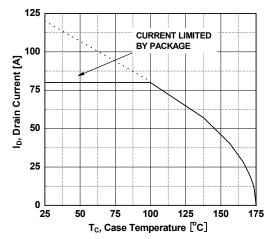
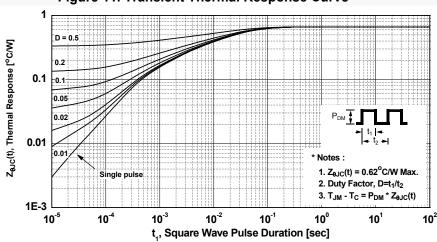


Figure 11. Transient Thermal Response Curve



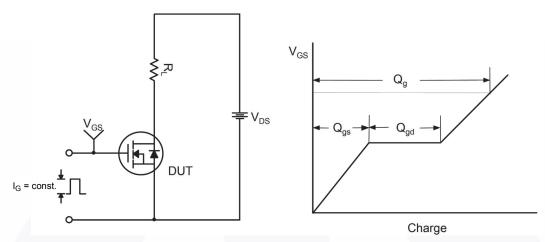


Figure 12. Gate Charge Test Circuit & Waveform

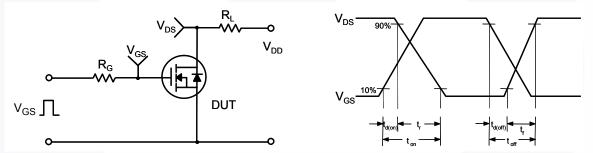


Figure 13. Resistive Switching Test Circuit & Waveforms

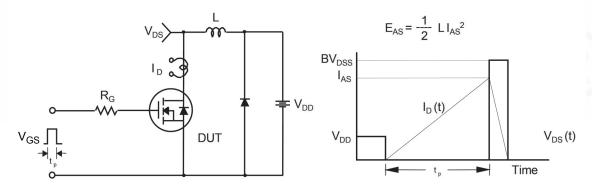


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

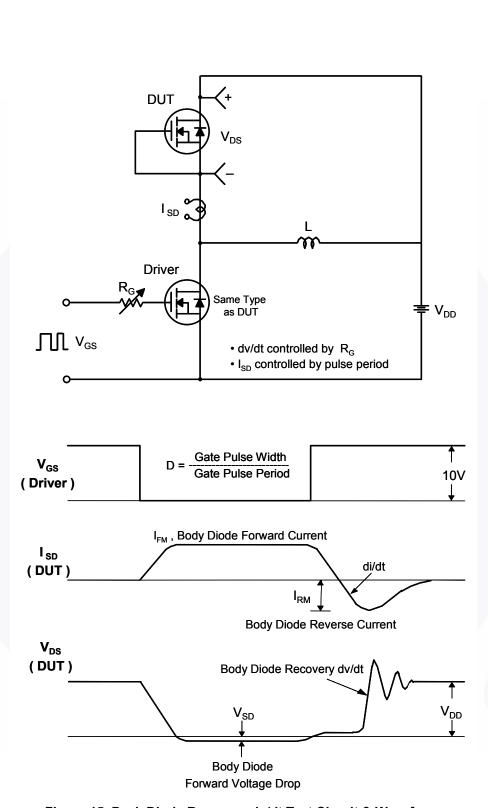


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

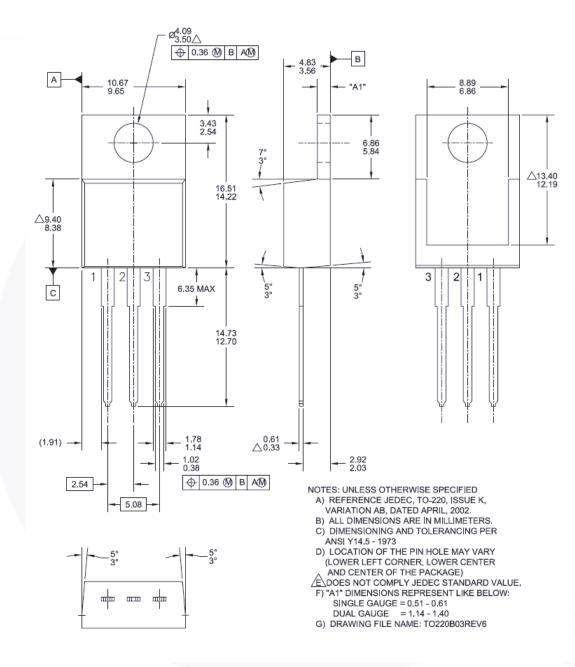


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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